

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	"10760463"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:03
L2	1	"10/760463"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:05
L3	6279	(substrate same gate same electrode same depth)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:06
L4	3844	(substrate same gate same electrode same depth same (dope or doping or doped or impurity or implant or implanting or implanted or implantation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:06
L5	4291	(substrate same gate same electrode same depth same (dope or doping or doped or impurity or implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:06
L6	2954	(substrate same gate same electrode same depth same (dope or doping or doped or impurity or implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) same (source or drain or source/drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:07
L7	777	(substrate same gate same electrode same depth same (dope or doping or doped or impurity or implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) same (source or drain or source/drain) same (sidewall or side-wall or (side near wall)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:07

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L8	350	(substrate same gate same electrode same (((first or second or third) near depth) or deeper) same (dope or doping or doped or impurity or implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) same (source or drain or source/drain) same (sidewall or side-wall or (side near wall)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:08
L9	203	(substrate same gate same electrode same (((first or second or third) near depth) or deeper) same surface same (dope or doping or doped or impurity or implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) same (source or drain or source/drain) same (sidewall or side-wall or (side near wall)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:10
L10	112	(substrate same gate same electrode same (((first or second or third) near depth) or deeper) same surface same (dope or doping or doped or impurity or implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) same (source or drain or source/drain) same (sidewall or side-wall or (side near wall))) same (method or process)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:12
L11	403	(substrate same gate same electrode same (((first or second or third) near2 depth) or deeper or shallower or shallow) same surface same (dope or doping or doped or impurity or implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) same (source or drain or source/drain) same (sidewall or side-wall or (side near wall))) same (method or process)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:12

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L12	64	((substrate same gate same electrode same (((first or second or third) near2 depth) or deeper or shallower or shallow) same surface same (dope or doping or doped or impurity or implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) same (source or drain or source/drain) same (sidewall or side-wall or (side near wall))) same (method or process)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:13
L13	20	((substrate same gate same electrode same (surface near10 (((first or second or third) near2 depth) or deeper or shallower or shallow)) same (dope or doping or doped or impurity or implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) same (source or drain or source/drain) same (sidewall or side-wall or (side near wall))) same (method or process)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:14
L14	24	((substrate same gate same electrode same (surface with (((first or second or third) near2 depth) or deeper or shallower or shallow)) same (dope or doping or doped or impurity or implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) same (source or drain or source/drain) same (sidewall or side-wall or (side near wall))) same (method or process)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:14
L15	15	((substrate same gate same electrode same (surface with (((first or second or third) near2 depth) or deeper or shallower)) same (dope or doping or doped or impurity or implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) same (source or drain or source/drain) same (sidewall or side-wall or (side near wall))) same (method or process)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:16

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L16	10	((substrate same gate same electrode same (surface with (((first or second or third) near2 depth) or deeper or shallower)) same (dope or doping or doped or impurity or implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) same (source or drain or source/drain) same (sidewall or side-wall or (side near wall))) same (method or process)).clm. and ((junction near capacitance) or ((leak or leakage) near current) or (short near channel))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:17
L17	10	((substrate same gate same electrode same (surface with (((first or second or third) near2 depth) or deeper or shallower)) same (dope or doping or doped or impurity or implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) same (source or drain or source/drain) same (sidewall or side-wall or (side near wall))) same (method or process)).clm. and ((junction near capacitance) or ((leak or leakage) near current) or (short near channel near effect))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:21
L18	6	(257/408 or 257/344 or 257/335 or 438/305 or 438/306 or 438/307 or 438/200 or 438/199) and ((substrate same gate same electrode same (surface with (((first or second or third) near2 depth) or deeper or shallower)) same (dope or doping or doped or impurity or implant or implanting or implanted or implantation or diffuse or diffusing or diffused or diffusion) same (source or drain or source/drain) same (sidewall or side-wall or (side near wall))) same (method or process)).clm. and ((junction near capacitance) or ((leak or leakage) near current) or (short near channel near effect))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:24

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L19	4	l15 and (third near depth).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:25
L20	0	l15 and oki	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 08:25